Silicon N-Channel MOS FET

HITACHI

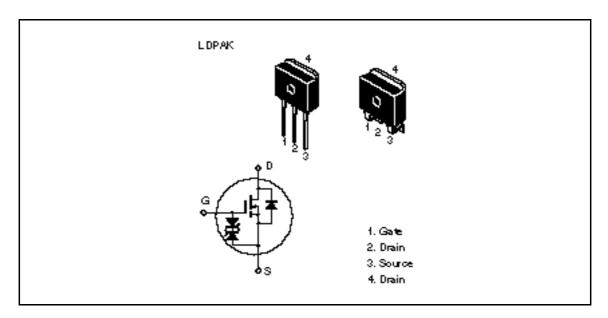
Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator and DC-DC converter

Outline





Absolute Maximum Ratings (Ta = 25° C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	250	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	Ι _D	15	А
Drain peak current	I(pulse) ^{★1}	60	А
Body to drain diode reverse drain current	I _{DR}	15	А
Channel dissipation	Pch*2	75	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

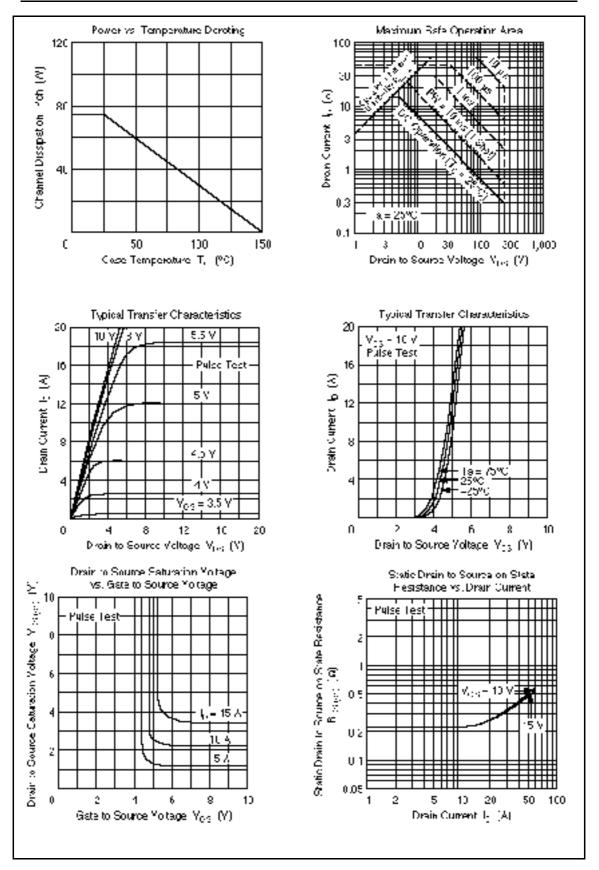
Notes 1. PW 10 µs, duty cycle 1%

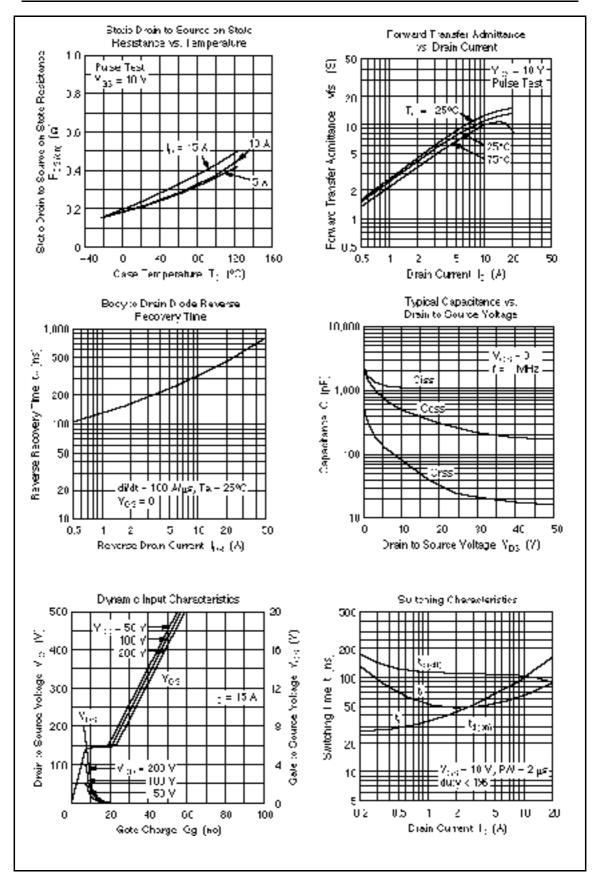
2. Value at $T_c = 25^{\circ}C$

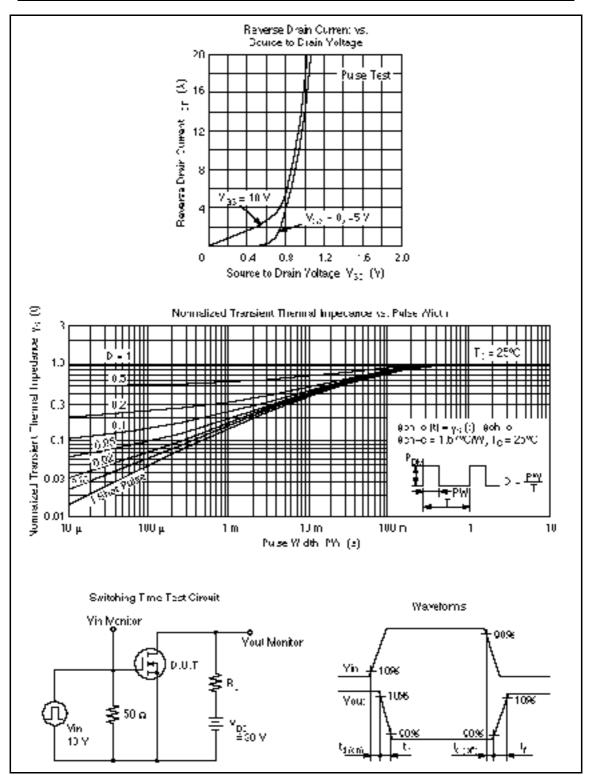
Electrical Characteristics (Ta = 25° C)

Symbol	Min	Тур	Max	Unit	Test conditions
$V_{(\text{BR})\text{DSS}}$	250	_	_	V	$I_{\rm D} = 10$ mA, $V_{\rm GS} = 0$
$V_{(BR)GSS}$	±30	_	_	V	$I_{G} = \pm 100 \ \mu A, \ V_{DS} = 0$
I _{GSS}		_	±10	μA	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0$
t I _{DSS}		_	250	μA	$V_{\rm DS} = 200 \ V, \ V_{\rm GS} = 0$
$V_{GS(off)}$	2.0	_	3.0	V	$I_{\rm D} = 1 \text{ mA}, V_{\rm DS} = 10 \text{ V}$
	_	0.22	0.27		$I_{D} = 8 \text{ A}, V_{GS} = 10 \text{ V}^{*1}$
yfs	6.0	10.0		S	$I_{\rm D} = 8 \text{ A}, V_{\rm DS} = 10 \text{ V}^{*1}$
Ciss		1250	_	pF	$V_{\rm DS} = 10 \ V, \ V_{\rm GS} = 0,$
Coss	_	510	_	pF	f = 1 MHz
Crss	_	85	_	pF	_
t _{d(on)}		24	_	ns	$I_{\rm D} = 8 \text{ A}, V_{\rm GS} = 10 \text{ V},$
t,	_	85	_	ns	R _L = 3.75
$t_{d(off)}$		110	_	ns	_
t _f		60	_	ns	—
V_{DF}	_	1.0	_	V	$I_{F} = 15 \text{ A}, V_{GS} = 0$
t _{rr}	_	400		ns	$I_{_{\rm F}} = 15$ A, $V_{_{\rm GS}} = 0$, $di_{_{\rm F}}/dt = 100$ A/µs
	V(BR)DSS V(BR)GSS I _{GSS} I _{DSS} V(BR)GSS I _{GSS} I _{DSS} VGS(off) RDS(on) Iyfs Ciss Coss Crss t _{d(on)} t _f V _{d(off)} V _{DF}	$\begin{array}{c c} V_{(BR)DSS} & 250 \\ \hline V_{(BR)GSS} & \pm 30 \\ \hline I_{GSS} & \\ \hline I_{DSS} & \\ \hline V_{GS(off)} & 2.0 \\ \hline R_{DS(on)} & \\ \hline V_{SS(off)} & 6.0 \\ \hline Ciss & \\ \hline Coss & \\ \hline Coss & \\ \hline Crss & \\ \hline t_{d(off)} & \\ \hline t_{q(off)} & \\ \hline t_{f} & \\ \hline V_{DF} & \\ \hline \end{array}$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

Note 1. Pulse test







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